

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

Listing of Claims:

Claims 1-5 (Cancelled)

6. (Currently amended) A semiconductor device, comprising:

a substrate,

a first dielectric film overlying said substrate, said first dielectric film having a pair of trenches formed therein apart from each other,

a pair of fuse terminals each embedded in ~~a surface portion~~ an associated one of said pair of trenches of said first dielectric film, and

a fuse element formed on said first dielectric film ~~and connected to~~ in electrical contact with said pair of fuse terminals.

7. (Original) The semiconductor device as defined in claim 6, further comprising a plurality of top interconnect lines each having a line body formed as a common layer with said fuse terminals and a protective film formed on said line body as a common layer with said fuse element.

8. (Original) The semiconductor device as defined in claim 6, further comprising a plurality of electrode pads each having a pad body formed as a common layer with said fuse terminals and a protective film formed on said pad body as a common layer with said fuse element.

9. (Currently amended) The semiconductor device, ~~as defined in claim 7, further~~ comprising:

a substrate;

a first dielectric film overlying said substrate;

a pair of fuse terminals embedded in a surface portion of said first dielectric film;

a fuse element formed on said first dielectric film and connected to said pair of fuse terminals;

a second dielectric film formed [[on]] to cover said first dielectric film and said fuse element; and having a plurality of openings each exposing one of said electrode pads

a third dielectric film formed on said second dielectric film; and

an opening formed in said third dielectric film to expose a part of said second dielectric film above said fuse element.

10. (Original) The semiconductor device as defined in claim 9, wherein said fuse element is made of TiN film, stacked films including TiN film and a Ti film or a TiW film.

11. (Original) The semiconductor device as defined in claim 9, wherein said fuse terminals are made of Al, Al alloy, Cu or Cu alloy.

Claims 12-14 (Cancelled)

15. (New) A semiconductor device, comprising:

a substrate;

a first dielectric film overlying said substrate;

first, second and third trenches formed in said first dielectric film apart from one another;

first and second fuse terminals embedded respectively in said first and second trenches of said first dielectric film;

an interconnection line embedded in said third trench of said first dielectric film;

a fuse element formed on said first dielectric film in electrical contact with said first and second fuse terminals; and

a first conductive film formed on said interconnection line in contact therewith.

16. (New) The semiconductor device as defined in claim 15, wherein said fuse element and said first conductive film are made of the same material as each other.

17. (New) The device as defined in claim 16, further comprising:

a fourth trench formed in said first dielectric film apart from said first, second and third trenches;

an electrode pad embedded in said fourth trench of said first dielectric film; and

a second conductive film formed on said electrode pad in contact therein, said second conductive film being made of the same material as said first conductive film.

18. (New) The device as defined in claim 17, further comprising:

a second dielectric film formed to cover said first dielectric film, said fuse element and said first and second conductive films;

a third dielectric film formed on said second dielectric film;

a first opening formed in said third dielectric film to expose a part of said second dielectric film above said fuse element; and

a second opening formed in said third and second dielectric films to expose a part of said electrode pad.

19. (New) The device as defined in claim 16, wherein said fuse terminals and said interconnection line are made of the same material as each other.

20. (New) The device as claimed in claim 17, wherein said fuse element, said first conductive film and said second conductive film are made of the same materials as one another.

21. (New) The device as defined in claim 20, wherein said fuse terminals, said interconnection line and said electrode pad are made of the same material as one another.

22. (New) The device as defined in claim 6, wherein said fuse element is formed all over said pair of fuse terminals.

23. (New) The device as defined in claim 9, wherein said fuse element is formed all over said pair of fuse terminals.

24. (New) The device as defined in claim 15, wherein said fuse element is formed all over said pair of fuse terminals and said first conductive film is formed all over said interconnection line.
25. (New) The device as defined in claim 17, wherein said fuse element is formed all over said pair of fuse terminals, said first conductive film is formed all over said interconnection line and said second conductive film is formed all over said electrode.